

## FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 20461

Generic Copy

#### Issue Date: 28-Apr-2014

**<u>TITLE</u>**: Qualification of ON Semiconductor Vietnam (OSV) for the Assembly and Test of Trench IGBT and a transition to a new case outline of Rectifiers devices for package TO247.

#### PROPOSED FIRST SHIP DATE: 28-Jul-2014

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Assembly & Test

#### FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or following contact Product Engineer: Raja Roziah Raja Rahmat <<u>Raja.Roziah.Rahmat@onsemi.com></u>

**SAMPLES**: Contact your local ON Semiconductor Sales Office

#### ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Reliability Engineer Chean Ching Sim <<u>cheanching.sim@onsemi.com</u>>

#### NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

#### DESCRIPTION AND PURPOSE:

This FPCN announces the planned capacity expansion of ON Semiconductor's assembly and test operations of TO247 packaged rectifiers and trench IGBTs. Currently, assembly and test of these devices is performed at Nantong Fujitsu Microelectronics (NMFE), China. ON Semiconductor Vietnam (OSV) is being added as an additional assembly and test site.

Legacy rectifier products will transition to a new case outline as a part of this capacity expansion. Case outline 340L-02 will transition to 340AL. This does not impact the IGBT devices listed in this FPCN.

Upon the expiration of this FPCN, TO247 for the affected devices will be produced in either of the two locations, Nantong Fujitsu Microelectronics (NMFE) or On Semiconductor Vietnam (OSV). These products have been qualified to industrial requirements. These products will be Pb-free, Halide free and RoHS compliant.

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## **RELIABILITY DATA SUMMARY:**

## MBR7030WTG

Test:	Conditions:	Interval:	Results
Autoclave	Ta =121°C RH=100% 15 psig	96 hrs	0/80
тс	Ta = -65°C to 150°C	1000 cycles	0/80
H3TRB	Ta = 85°C RH=85%	1008 hrs	0/80
	Bias = 80% rated V or 100V Max		
IOL	Ta = 25°C, Delta TJ = 100°C,	6000 cycles	0/80
	Ton/off = 5 min.	-	
HTRB	Ta = 90°C 80% Rated Voltage	1008 hrs	0/80
HTSL	Ta = 150°C	1008 hrs	0/80
RSH	Ta = 260°C, 10 sec dwell		0/30
Solderability	Steam Aging = 8hrs	8 hrs	0/15

### MUR3060WTG

Test: Conditions:		Interval:	<b>Results</b>	
Autoclave	Ta =121°C RH=100% 15 psig	96 hrs	0/80	
TC	Ta = -65°C to 150°C	1000 cycles	0/80	
H3TRB	Ta = 85°C RH=85%	1008 hrs	0/80	
	Bias = 80% rated V or 100V Max			
IOL	Ta = 25°C, Delta TJ = 100°C,	6000 cycles	0/80	
	Ton/off = 5 min.	-		
HTRB	Ta = 150°C 80% Rated Voltage	1008 hrs	0/80	
HTSL	Ta = 150°C	1008 hrs	0/80	
RSH	Ta = 260°C, 10 sec dwell		0/30	
Solderability	Steam Aging = 8hrs	8 hrs	0/15	

## NGTB40N135IHRWG

Test:	Conditions:	Interval:	Results
Autoclave	Ta =121°C RH=100% 15 psig	96 hrs	0/80
тс	Ta = -65°C to 150°C	1000 cycles	0/80
H3TRB	Ta = 85°C RH=85%	1008 hrs	0/80
	Bias = 80% rated V or 100V Max		
IOL	Ta = 25°C, Delta TJ = 100°C,	6000 cycles	0/80
	Ton/off = 5 min.		
HTRB	Ta = 145°C 80% Rated Voltage	1008 hrs	0/80
HTGB	Ta = 150°C 100% Rated Voltage	1008 hrs	0/80
HTSL	Ta = 150°C	1008 hrs	0/80
RSH	Ta = 260°C, 10 sec dwell		0/30
Solderability	Steam Aging = 8hrs	8 hrs	0/15

### **ELECTRICAL CHARACTERISTIC SUMMARY:**

There are no changes in electrical characteristics; product performance meets data sheet specifications. Characterization data is available upon request.

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## **CHANGED PART IDENTIFICATION:**

Product from On Semiconductor Vietnam will be marked with site code VN prior to date code.

### Comparison between case outline

TO-247 CASE 340L-02



TO-247 CASE 340AL



NOTES

1.

ES: DMENSIONING AND TOLEPANCING PER ASME Y14 5M, 1994. CONTROLLING DIMENSION: MILLMETERS. 8.0 T REQUIRED, NOTCH MAY BE ROUNDED. DMENSIONS DAND E OD NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DMENSIONS ARE MASURED AT THE OUTERMOIST BATTRING OF THE PLASTIC ROOV. LEND FINISH IS UNCONTROLLED IN THE REGION DERINED BY 11 4

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(2) SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5°TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED

	BY L1.				
		MILUMETERS			
	DIM	MN	MAX		
	A	470	5.30		
	A1	220	2.60		
	b	1.00	1.40		
	12	1節	2.35		
	z	260	3.40		
	0	0.40	0.80		
	D	2030	21.40		
	E	1550	16.25		
	Ð	432	5.49		
		5.45BSC			
	L	19.80	20.80		
	Lt	3.50	4.50		
	P	3.55	3.65		
	0	5.40	6.20		
	8	6 15 BSC			

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## List of affected General Parts: Rectifier

MBR3045WTG MBR4015LWTG MBR6045WTG MBR60L45WTG MBR7030WTG MUR3020WTG MUR3040WTG MUR3060WTG MBR40H100WTG

List of affected General Parts: Trench IGBT

NGTB15N120IHRWG NGTB15N135IHRWG NGTB20N120IHRWG NGTB20N135IHRWG NGTB30N120IHRWG NGTB30N135IHRWG NGTB40N120IHRWG NGTB40N135IHRWG